

II. Claims 1-13, drawn to a substrate, classified in class 148, subclass 33.3.

The Examiner asserts that the claims of Group I and Group II are distinct on grounds that the substrate of Group II can be produced by another material different process than that of claim 26, such as one which deposits only a first dielectric layer on the SiC layer, and from that of claim 14, in which no noble gas is present in the chamber.

Applicants elect Group I, claims 14-29, with traverse. Claims 14-29 recite a method for forming a silicon carbide layer on a substrate and depositing another layer *in situ* with the silicon carbide layer. Claims 1-13 recite a substrate having a silicon carbide layer having a dielectric constant less than 7.0 and a first dielectric layer deposited on the silicon carbide layer *in situ* with the silicon carbide layer. Applicants believe that the Examiner has not sufficiently distinguished the claims for restriction because the basis of the restriction of depositing a second dielectric layer is not accurate since a second dielectric layer is disclosed in claims 2 and 4 of Group II. In view of the above, Applicants request modification of the restriction requirement to permit prosecution of claims 1-29.

Applicants submit that this amendment raises no new issues and introduces no new matter. Having addressed all issues set out in this restriction requirement, Applicants respectfully requests withdrawal of the restriction requirement and a favorable action on all pending claims.

Respectfully submitted,



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APPENDIX

1. (Amended) A substrate, comprising:
 - [a]] a silicon carbide layer having a dielectric constant less than 7.0 and deposited on the substrate; [and]
 - [b]] a first dielectric layer deposited on the silicon carbide layer *in situ* with the silicon carbide layer; and
 - a photoresist layer deposited on the first dielectric layer.

14. (Amended) A method of forming a silicon carbide layer on a substrate, comprising:
 - [a]] introducing silicon, carbon, and a noble gas into a chamber;
 - [b]] initiating a plasma in the chamber;
 - [c]] reacting the silicon and the carbon in the presence of the plasma to form silicon carbide;
 - [d]] depositing a silicon carbide layer having a dielectric constant less than 7.0 on the substrate in the chamber; [and]
 - [e]] depositing a first dielectric layer *in situ* [with] on the silicon carbide layer; and
 - depositing a photoresist layer on the first dielectric layer.

15. (Amended) The method of claim 14, further comprising:
 - [a]] depositing a silicon carbide etch stop *in situ* [with] on the first dielectric layer;
 - [b]] depositing a second dielectric layer *in situ* [with] on the silicon carbide etch stop.

16. (Amended) The method of claim 15, further comprising depositing a silicon carbide anti-reflective coating *in situ* [with] on the second dielectric layer.

18. (Amended) The method of claim [14] 19, further comprising depositing a photoresist layer on [the first dielectric layer] the silicon carbide anti-reflective coating.

19. (Amended) The method of claim 14, further comprising depositing a silicon carbide anti-reflective coating *in situ* [with] on the first dielectric layer.

26. (Amended) A method of *in situ* deposition of silicon carbide on a substrate, comprising:

[a)] depositing a silicon carbide barrier layer on the substrate;

[b)] depositing a first dielectric layer on the barrier layer *in situ* [with] on the barrier layer;

[c)] depositing an etch stop on the first dielectric layer *in situ* [with] on the first dielectric layer;

[d)] depositing a second dielectric layer on the etch stop *in situ* [with] on the etch stop; [and]

[e)] depositing [an] a silicon carbide anti-reflective coating on the second dielectric layer *in situ* [with] on the second dielectric layer; and
depositing a photoresist layer on the silicon carbide anti-reflective coating.